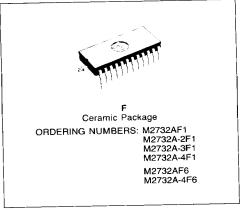


32K (4K×8) UV ERASABLE PROM

- FAST ACCESS TIME: 200ns MAX M2732A-2F1 250ns MAX M2732AF1/M2732AF6 300ns MAX M2732A/-3F1 450ns MAX M2732A-4F1/M2732A-4F6
- SINGLE +5V POWER SUPPLY
- LOW STANDBY CURRENT 35mA MAX
- INPUTS AND OUTPUTS TTL COMPATIBLE DURING READ AND PROGRAM
- COMPLETELY STATIC

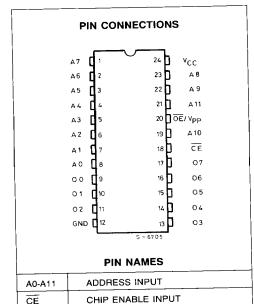


DESCRIPTION

The M2732A is a 32,768-bits ultraviolet erasable and electrically programmable read-only memory (EPROM). It is organized as 4,096 words by 8 bits and manufactured using SGS' N-channel Si-Gate MOS process. The M2732A with its single +5V power supply and with an access time of 200ns, is ideal for use with the high performance +5V microprocessors such as the Z8®, Z80® and Z8000™. The M2732A has an important feature which is the separate output control, Output Enable (OE) from the Chip Enable control (CE). The OE control elimitates bus contention in multiple bus microprocessor systems.

The M2732A also features a standby mode which reduces the power dissipation without increasing access time. The active current is 125 mA while the maximum standby current is only 35 mA a 70% saving. The standby mode is achieved by applying a TTL-high signal to the CE input.

The M2732A is available in a 24-lead dual in-line ceramic package glass lens (frit-seal).



OUTPUT ENABLE INPUT

DATA INPUT/OUTPUT

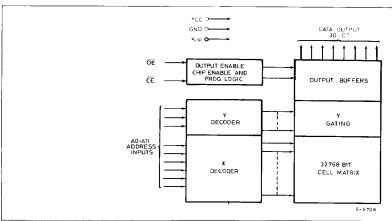
CF

ŌE

00-07



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
VI	All Input or Output voltages with respect to ground	+ 6 to -0.6	٧
V _{PP}	Supply voltage with respect to ground during program	+ 22 to - 0.6	V
Tamb	Ambient temperature under bias F1/-2F1/-3F1/-4F1 F6/4F6	- 10 to + 80 - 50 to + 95	°C
T _{stq}	Storage temperature range	- 65 to + 125	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating or and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

OPERATING MODES

MODE	PINS CE (18)	OE/V _{PP} (20)	V _{CC} (24)	OUTPUTS (9-11, 13-17)
READ	V _{IL}	V _{IL}	+5	D _{OUT}
STANDBY	V _{IH}	Don't Care	+5	High Z
PROGRAM	V _{IL}	V _{PP}	+5	D _{IN}
PROGRAM VERIFY	V _{IL}	V _{IL}	+5	D _{OUT}
PROGRAM INHIBIT	V _{IH}	V _{PP}	+5	High Z

READ OPERATION DC AND AC CONDITIONS

	F1/ - 2F1 3F1/ 4F1	F6/ - 4F6
Operating Temperature Range	0 to 70°C	− 40 to 85°C
V _{CC} Power Supply (1,2)	5V ±5%	5V ±5%
V _{PP} Voltage ⁽²⁾	V _{PP} = V _{CC}	$V_{PP} = V_{CC}$

DC AND OPERATING CHARACTERISTICS

Symbol					Unit	
	Parameter	Test Conditions	Min.	Typ.(3)	Max.	Unit
	Input Load Current	V _{IN} = 5.5V			10	μ A
الده	Output Leakage Current	V _{OUT} = 5.5V			10	μA
ICC1(2)	V _{CC} Current Standby	CE = V _{IH} OE = V _{IL}	-		35	mA
ICC2(2)	V _{CC} Current Active	CE = OE = V _{II}		70	125	mA
VIL	Input Low Voltage		- 0.1		+ 0.8	\
VIH	Input High Voltage		2.0		V _{CC} +1	V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA			0.45	V
VoH	Output High Voltage	I _{OH} = 400 μA	2.4	<u> </u>	<u> </u>	V

CHARACTERISTICS

- CONF	HACTERISTICS	Test M2		732A-2 M27		M2732A		32A-3	M2732A-4		Unit
Symbol	Parameter	Conditions	Min	Max	Min	Max	Min	Max	Min	Max	
	Address to Output Delay	CE = OE = V _{II}		200		250		300		450	ns
tACC	CE to Output Delay	OE = V _{II}		200		250		300		450	ns
t _{CE}	OE to Output Delay	CE = V _{II}		100		100		150		150	ns
toe	OE High to Output Float	CE = VII	0	60	0	60	0	130	0_	130	ns
t _{DF(4)}	Output Hold from Addresses	=	0		0		0		0		ns
i	CE or OE Whichever Occurred First										

CAPACITANCE (4) (T_{amb} = 25°C, f = 1MHz)

			Values			
Parameter	Test conditions	Min.	Тур.	Max.	Unit	
C _{IN 1} Input Capacitance excepet OE/V _{PP}	V _{IN} = 0		4	6	pF	
C _{IN 2} OE/V _{PP} Input capacitance	V _{IN} = 0			20	pF	
Output capacitance	V _{OUT} = 0		8	12	ρF	

 v_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP} . V_{PP} may be connected directly to V_{CC} except during programming. The supply current would then be the sum of I_{CC} and I_{PP} . Typical values are for I_{amb} = 25°C and nominal supply voltages. This parameter is only sampled and is not 100% tested



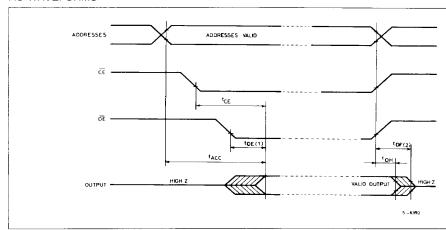
AC TEST CONDITIONS

Output Load: 100pF+1TTL Gate Input Rise and Fall Times: ≤ = 20ns Input Pulse Levels: 0.45 to 2.4V

Timing Measurement Reference Levels: Inputs 0.8 and 2V

Outputs 0.8 and 2V

AC WAVEFORMS



Notes

- 1. $\overline{\text{OE}}$ may be delayed up to t_{ACC} t_{OE} after the falling edge $\overline{\text{CE}}$ without impact on t_{ACC}.
- 2. t_{DF} is specified from $\overline{\text{OE}}$ or $\overline{\text{CE}}$ whichever occurs first.

READ MODE

The M2732A has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (CE) is the power control and should be used for device selection. Output Enable (OE) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to delay from CE to output (tCE). Data is available at the outputs after the falling edge of OE, assuming that CE has been low and addresses have been stable for at least t_{ACC}-toE.

STANDBY MODE

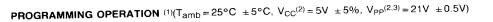
The M2732A has a standby mode which reduces the active power current by 70%, from 125mA to 35mA. The M2732A is placed in the standby mode by applying a TTL high signal to \overline{CE} input. When in standby mode, the outputs are in a high impedance state, independent of the \overline{OE} input.

OUTPUT OR-TIEING

Because M2732A's are usually used in larger mory arrays, the product features a 2 line contribunction which accommodates the use of multip memory connection. The two line control functionallows:

- a) the lowest possible memory power dissipation b) complete assurance that output bus contention
- b) complete assurance that output bus contention will not occur.

To most efficiently use these two control lines, is recommended that \overline{CE} be decoded and used at the primary device selecting function, while \overline{CE} should be made a common connection to all devices in the array and connected to the READ lifted from the system control bus. This assures that a deselected memory devices are in their low powers standby mode and that the output pins are only a tive when data is desired from a particular memory device.



DC AND OPERATING CHARACTERISTIC:

Symbol	Parameter	Conditions			Unit	
			Min.	Тур.	Max.	Unit
ILI	Input Current (All Inputs)	$V_{IN} = V_{IL}$ or V_{IH}			10	μΑ
V _{IL}	Input Low Level		- 0.1		0.8	V
VIH	Input High Level		2.0		V _{CC} + 1	٧
VOL	Output Low Voltage During Verify	I _{OL} = 2.1 mA			0.45	
VoH	Output High Voltage During Verify	I _{OH} = -400 μA	2.4			V
lcc2	V _{CC} Supply Current (Active)			70	125	mA
IPP	V _{PP} Supply Current	$\overline{CE} = V_{IL}, \overline{OE} = V_{PP}$			30	mA

AC CHARACTERISTICS

				Unit		
Symbol	Parameter	Test conditions	Min. Typ. Max. 2 2 2 0 2 0 130			
tas	Address Set Up Time		2			μS
toes	OE Set Up Time		2			μS
t _{DS}	Data Set Up Time		2			μS
t _{AH}	Address Hold Time		0			μS
t _{DH}	Data Old Time		2			μS
t _{DF}	Chip Enable to Output Float Delay		0		130	ns
t _{DV}	Data valid from CE	$\overline{CE} = V_{IL}, \ \overline{OE} = V_{IL}$			1	μS
tew	CE Pulse Width During Programming		45	50	55	ms
terr	OE Pulse rise time During Programming		50			ns
tvB	V _{PP} recovery time		2			μS

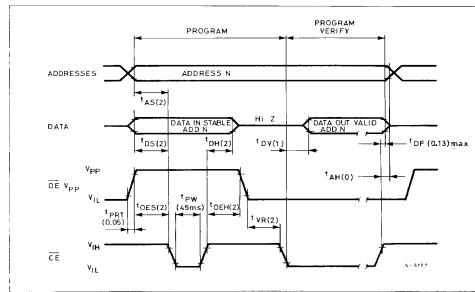
1 SGS guarantees the product only if it is programmed to specifications described herein. Notes:

^{2.} V_{CC} must be applied simultaneusly with or before V_{PP} and removed simultaneously with or after V_{PP}. The M2732A must not be inserted into or removed from a board with Vpp at 21±0.5V or damage may occur to the device.

^{3.} The maximum allowable voltage which may be applied to the V_{PP} pin during programming is +22V. Care must be taken when switching the V_{PP} supply to prevent overshoot exceeding this 22V maximum specification.



PROGRAMMING WAVEFORMS



- All times shown in () are minimum and in μsec unless otherwise specified.
- 2. The input timing reference level is 1V for V_{IL} and 2V for V_{IH} .
- 3. toE and toF are characteristics of the device but must be accomodated by the programmer.

PROGRAMMING

Caution: Exceeding 22V on pin (V_{PP}) will damage the M2732A.

When delivered, and after each erasure, all bits of the M2732A are in the "1" state. Data is introduced by selectively programming "0's" into the desired bit locations. Although only "0's" will be programmed, both "1's" and "0's" can be presented in the data word. The only way to change a "0" to a "1" is by ultraviolet light erasure.

The M2732A is in the programming mode when the $\overline{\text{OE}/\text{Npp}}$ input is at 21V. It is required that a 0.1 μF capacitor be placed across $\overline{\text{OE}/\text{Npp}}$ and ground to suppress spurious voltage transients which may damage the device. The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL.

When the address and data are stable, a 50 msec, active low, TTL program pulse is applied to the

CE input. A program pulse must be applied at ea address location to be programmed. You can p gram any location at any time — either individuly, sequentially, or at random. The program pul has a maximum width of 55 msec. The 2732A mont be programmed with a DC signal applied to to CE input.

Programming of multiple 2732As in parallel with the same data can be easily accomplished due to the simplicity of the programming requirements. Linguist of the paralleled M2732As may be continued together when they are programmed with the same data. A low level TTL pulse applied to the time to the transfer of the paralleled 2732As.

PROGRAM INHIBIT

Programming of multiple 2732As in parallel with efferent data is also easily accomplished. Except CE, all like inputs (including OE) of the para

2732As may be common. <u>A TTL level program</u> pulse applied to a 2732A's CE input with OE/Vpp at 21V will program that 2732A. A high level CE input inhibits the other 2732As from being programmed.

PROGRAM VERIFY

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify is accomplished with OE/Vpp and CE at V_{IL}.

ERASURE OPERATION

The erasure characteristics of the M2732A are such that erasure begins when the cels are exposed to light with wavelengths shorter than approximately 4000 Angstroms (A). It should be noted that sunlight and certain types of fluorescent lamps have

wavelengths in the 3000-4000 A range. Data shows that constant exposure to room level fluorescent lighting could erase a typical M2732A in approximately 3 years, while it would take approximately 1 week to cause erasure when exposed to the direct sunlight. If the M2732A is to be exposed to these types of lighting conditions for extended periods of time, it is suggested that opaque labels to put over the M2732A window to prevent unintentional erasure.

erasure. The recommended erasure procedure for the M2732A is exposure to shortwave ultraviolet light which has a wavelength of 2537 Angstroms (A). The integrated dose (i.e. UV intensity \times exposure time) for erasure should be a minimum of 15 W-sec/cm². The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with 12000 μ W/cm² power rating. The M2732A should be placed within 2.5 cm of the lamp tubes during erasure. Some lamps have a filter on their tubes which should be removed before erasure.